

SPTECH Silicon NPN Power Transistor

BD801

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 100V(\text{Min})$
- Low Saturation Voltage
- Complement to Type BD802

APPLICATIONS

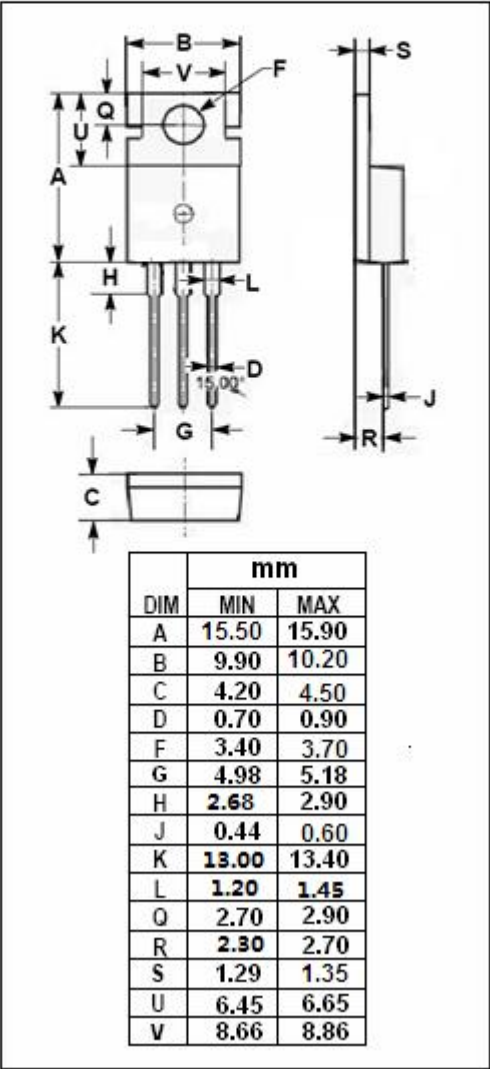
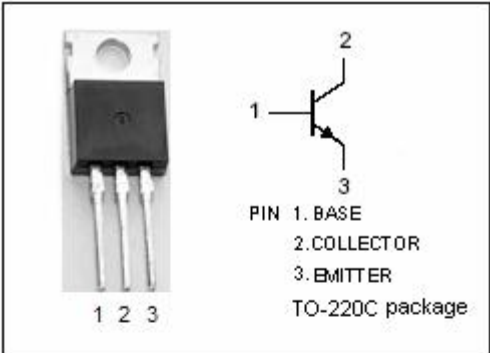
- Designed for a wide variety of medium-power switching and amplifier applications , such as series and shunt regulators and driver and output stages of high-fidelity amplifiers.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	100	V
V_{CEO}	Collector-Emitter Voltage	100	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	8	A
I_B	Base Current-Continuous	3	A
P_C	Collector Power Dissipation $T_C=25^{\circ}\text{C}$	65	W
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Ttemperature Range	-55~150	$^{\circ}\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance,Junction to Case	1.92	$^{\circ}\text{C/W}$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEQ(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=30\text{mA}; I_B=0$	100			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=3\text{A}; I_B=0.3\text{A}$			1	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=3\text{A}; V_{CE}=2\text{V}$			1.6	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=100\text{V}; I_E=0$			0.1	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			1	mA
h_{FE-1}	DC Current Gain	$I_C=1\text{A}; V_{CE}=2\text{V}$	30			
h_{FE-2}	DC Current Gain	$I_C=3\text{A}; V_{CE}=2\text{V}$	15			
f_T	Current-Gain—Bandwidth Product	$I_C=0.25\text{A}; V_{CE}=10\text{V}, f_{test}=1\text{MHz}$	3			MHz